Elektronische Bauelemente

# 2SB1132

**-1A, -40V**

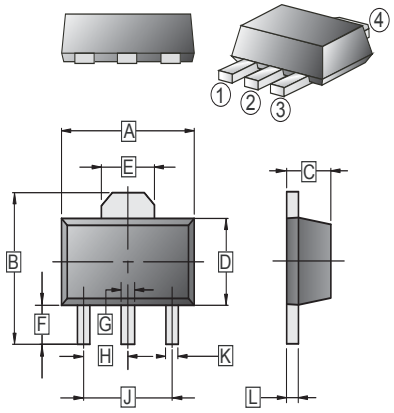
**PNP Silicon Medium Power Transistor**

RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

## FEATURES

- Low power dissipation 0.5W

**SOT-89**



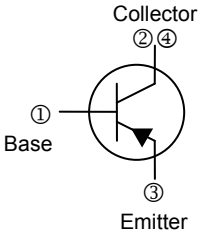

| REF. | Millimeter Min. | Millimeter Max. | REF. | Millimeter Min. | Millimeter Max. |
|---|---|---|---|---|---|
| A | 4.40 | 4.60 | G | 0.40 | 0.58 |
| B | 3.94 | 4.25 | H | 1.50 | TYP |
| C | 1.40 | 1.60 | J | 3.00 | TYP |
| D | 2.30 | 2.60 | K | 0.32 | 0.52 |
| E | 1.50 | 1.70 | L | 0.35 | 0.44 |
| F | 0.89 | 1.2 | | | |

## CLASSIFICATION OF $h_{FE}$

| Product Rank | 2SB1132-P | 2SB1132-Q | 2SB1132-R |
|---|---|---|---|
| Range | 82~180 | 120~270 | 180~390 |
| Marking | BAP | BAQ | BAR |

## PACKAGE INFORMATION

| Package | MPQ | Leader Size |
|---|---|---|
| SOT-89 | 1K | 7' inch |




## ABSOLUTE MAXIMUM RATINGS ($T_A$ = 25°C unless otherwise specified)

| Parameter | Symbol | Ratings | Unit |
|---|---|---|---|
| Collector-Base Voltage | $V_{CBO}$ | -40 | V |
| Collector-Emitter Voltage | $V_{CEO}$ | -32 | V |
| Emitter-Base Voltage | $V_{EBO}$ | -5 | V |
| Collector Current (DC) | $I_C$ | -1 | A |
| Collector Power Dissipation | $P_C$ | 500 | mW |
| Junction & Storage Temperature | $T_J$, $T_{STG}$ | 150, -55~150 | °C |

## ELECTRICAL CHARACTERISTICS ($T_A$ = 25°C unless otherwise specified)

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Test Conditions |
|---|---|---|---|---|---|---|
| Collector-base breakdown voltage | $V_{(BR)CBO}$ | -40 | - | - | V | $I_C$= -50μA, $I_E$=0 |
| Collector-emitter breakdown voltage | $V_{(BR)CEO}$ | -32 | - | - | V | $I_C$= -1mA, $I_B$=0 |
| Emitter-base breakdown voltage | $V_{(BR)EBO}$ | -5 | - | - | V | $I_E$= -50μA, $I_C$=0 |
| Collector cut-off current | $I_{CBO}$ | - | - | -0.5 | μA | $V_{CB}$= -20V, $I_E$=0 |
| Emitter cut-off current | $I_{EBO}$ | - | - | -0.5 | μA | $V_{EB}$= -4V, $I_C$=0 |
| DC current gain | $h_{FE}$ | 82 | - | 390 | | $V_{CE}$= -3V, $I_C$= -100mA |
| Collector-emitter saturation voltage | $V_{CE(sat)}$ | - | -0.2 | -0.5 | V | $I_C$= -500mA, $I_B$= -50mA |
| Transition frequency | $f_T$ | - | 150 | - | MHz | $V_{CE}$= -5V, $I_C$= -50mA, f=30MHz |
| Collector output capacitance | $C_{ob}$ | - | 20 | 30 | pF | $V_{CB}$= -10V, $I_E$=0, f=1MHz |

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## CHARACTERISTIC CURVES

